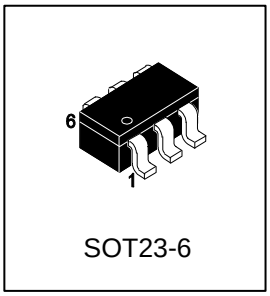
4-CHANNEL LOW CAPACITANCE ESD PROTECTION DIODES ARRAY

LRC8804AT1G

The LRC8804AT1G is a 4-channel ultra low capacitance rail clam ESD protection diodes array . Each channel consists of a pair of diodes that steer positive or negative ESD current to either the positive or negative rail . A zener diode is integrated in to the array between the positive and negative supply rails. In the typical applications, the negative rail pin (assigned as GND) is connected with system ground . The Positive ESD current is steered to the ground through an ESD diode and Zener diode and the positive ESD voltage is clamped to the zener voltage.

The LRC8804AT1G is idea to protect high speed data lines.

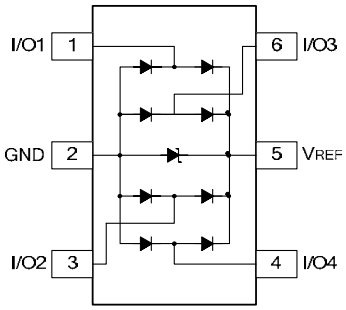


SOT23-6

●APPLICATIONS

1) HDMI / DVI ports
2)Display Port interface
3)10M / 100M / 1G Ethernet
4)USB 2.0 interface
4)VGA interface
5)Set-top box
6)Flat panel Monitors / TVs
7)PC / Note book

PIN CONFIGURATION



Top viev

●FEATURES

1) 4 channels of ESD protection;
2)Provides ESD protection to IEC61000-4-2 level 4
- ±25kV air discharge
- ±20kV contact discharge;

3) Channel I/O to GND capacitance: 0.6pF(Typ.)
4) Low clamping voltage;
5) Low operating voltage;
6) Ultra low leakage: nA level;
7) Optimized package for easy high speed data lines PCB layout;
8) RoHS compliant and Halogen Free;

●DEVICE MARKING AND ORDERING INFORMATION

Device	Shipping
LRC8804AT1G	3000Tape&Reel

LRC8804AT1G

●ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Limits	Unit
Peak Pulse Power(8/20us)	P_{PP}	75	W
Peak Pulse Current(8/20us)	I_{PP}	5	A
ESD per IEC 61000-4-2(Air)	V_{ESD1}	±25kV	kV
ESD per IEC 61000-4-2(Contact)	V_{ESD2}	±20kV	kV
Operating Temperature Range	Topr	-55 ~ +125	°C
Storage Temperature Range	Tstg	-55 ~ +150	°C

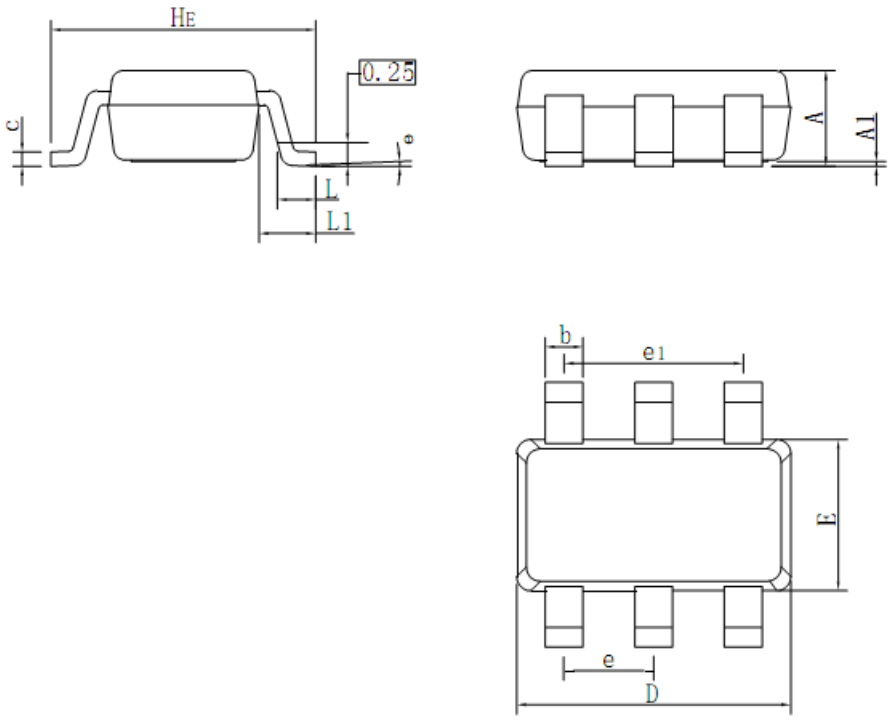
●ELECTRICAL CHARACTERISTICS (Ta= 25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Working Voltage	V_{RWM}	–	–	5	V	Any I/O pin to GND
Reverse Breakdown Voltage	V_{BR}	6	–	–	V	It =1mA; Any I/O pin to GND
Reverse Leakage Current	I_R	–	–	1	μA	V_{RWM} =5V, T=25°C; Any I/O pin to GND
Clamping Voltage	V_{C1}	–	–	10	V	I_{PP}=1A, t_P=8/20μs; Any I/O pin to GND
Clamping Voltage	V_{C2}	–	13	15	V	I_{PP}=5A, t_P=8/20μs; Any I/O pin to GND
Junction Capacitance Between Channel	C_{J1}	–	0.3	–	pF	V_R=0V, f=1MHz; Between I/O pins
Junction Capacitance Between I/O And GND	C_{J2}	–	0.6	0.8	pF	V_R=0V, f=1MHz; Any I/O pin to GND

LRC8804AT1G

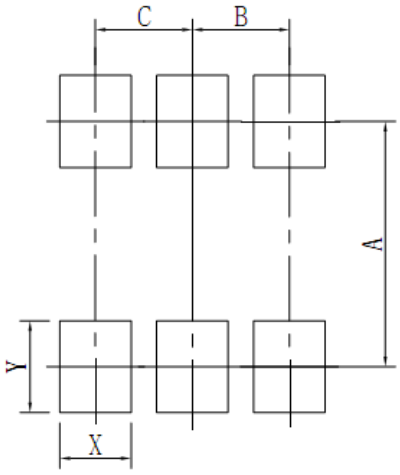
OUTLINE AND DIMENSIONS

SOT23-6



SOT23-6			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.40	0.50
c	0.10	0.17	0.26
D	2.80	2.90	3.10
E	1.30	1.60	1.70
e	0.85	0.95	1.05
e1	1.80	1.90	2.00
L	0.20	0.40	0.60
L1	0.60REF		
HE	2.50	2.80	3.00
θ	0°	-	10°

SOLDERING FOOTPRINT



SOT23-6	
DIM	(mm)
X	0.70
Y	0.90
A	2.40
B	0.95
C	0.95